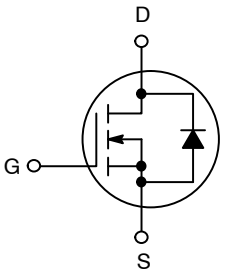
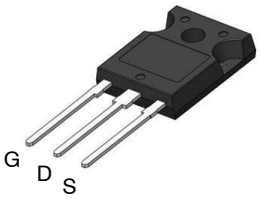
MOSFET - Power, N-Channel, SUPERFET III, FRFET

650 V, 95 mΩ, 36 A

NVHL095N65S3HF

V_{DSS}	$R_{DS(ON)}$ MAX	I_D MAX
650 V	95 mΩ @ 10 V	36 A





TO−247 Long Leads
CASE 340CX

Description

SUPERFET III MOSFET is **onsemi**'s brand−new high voltage super−junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This advanced technology is tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate.

Consequently, SUPERFET III MOSFET is very suitable for the various power system for miniaturization and higher efficiency.

SUPERFET III HF version provides fast recovery for improved efficiency in high speed switching applications.

Features

- 700 V @ T_J = 150°C
- Typ. $R_{DS(on)}$ = 78 mΩ
- Ultra Low Gate Charge (Typ. Q_g = 66 nC)
- Low Effective Output Capacitance (Typ. $C_{oss(eff.)}$ = 556 pF)
- 100% Avalanche Tested
- NVHL Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Automotive On Board Charger HEV−EV
- Automotive DC/DC Converter for HEV−EV

MARKING DIAGRAM



A	= Assembly Plant Code
YWW	= Data Code (Year & Week)
ZZ	= Assembly Lot Code
NVHL095N65S3HF	= Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

© Semiconductor Components Industries, LLC, 2020

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, Unless otherwise noted)

Symbol	Parameter		Value	Unit
V_{DSS}	Drain−to−Source Voltage		650	V
V_{GSS}	Gate−to−Source Voltage	− DC	±30	V
		− AC (f > 1 Hz)	±30	
I_D	Drain Current	− Continuous (T_C = 25°C)	36	A
		− Continuous (T_C = 100°C)	22.8	
I_{DM}	Drain Current	− Pulsed (Note 1)	90	A
E_{AS}	Single Pulsed Avalanche Energy (Note 2)		440	mJ
I_{AS}	Avalanche Current (Note 2)		4.6	A
E_{AR}	Repetitive Avalanche Energy (Note 1)		2.72	mJ
dv/dt	MOSFET dv/dt		100	V/ns
	Peak Diode Recovery dv/dt (Note 3)		50	
P_D	Power Dissipation	(T_C = 25°C)	272	W
		− Derate Above 25°C	2.176	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		−55 to +150	°C
T_L	Maximum Lead Temperature for Soldering, 1/8″ from Case for 5 seconds		300	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating: pulse−width limited by maximum junction temperature.
2. I_{AS} = 4.6 A, R_G = 25 Ω, starting T_J = 25°C.
3. I_{SD} ≤ 18 A, di/dt ≤ 200 A/μs, V_{DD} ≤ 400 V, starting T_J = 25°C.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction−to−Case, Max.	0.46	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction−to−Ambient, Max.	40	

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Packing Method	Reel Size	Tape Width	Quantity
NVHL095N65S3HF	NVHL095N65S3HF	TO−247	Tube	N/A	N/A	30 Units

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
BV_{DSS}	Drain−to−Source Breakdown Voltage	V_{GS} = 0 V, I_D = 1 mA, T_J = 25°C	650	–	–	V
		V_{GS} = 0 V, I_D = 1 mA, T_J = 150°C	700	–	–	V
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temperature Coefficient	I_D = 15 mA, Referenced to 25°C	–	0.63	–	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 650 V, V_{GS} = 0 V	–	–	10	μA
		V_{DS} = 520 V, T_C = 125°C	–	11	–	
I_{GSS}	Gate−to−Body Leakage Current	V_{GS} = ±30 V, V_{DS} = 0 V	–	–	±100	nA
ON CHARACTERISTICS						
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 0.86 mA	3.0	–	5.0	V
$R_{DS(on)}$	Static Drain−to−Source On Resistance	V_{GS} = 10 V, I_D = 18 A	–	78	95	mΩ
g_{FS}	Forward Transconductance	V_{DS} = 20 V, I_D = 18 A	–	19	–	S
DYNAMIC CHARACTERISTICS						
C_{iss}	Input Capacitance	V_{DS} = 400 V, V_{GS} = 0 V, f = 1 MHz	–	3105	–	pF
C_{oss}	Output Capacitance		–	65	–	pF
$C_{oss(eff.)}$	Effective Output Capacitance	V_{DS} = 0 V to 400 V, V_{GS} = 0 V	–	556	–	pF
$C_{oss(er.)}$	Energy Related Output Capacitance	V_{DS} = 0 V to 400 V, V_{GS} = 0 V	–	107	–	pF
$Q_{g(tot)}$	Total Gate Charge at 10 V	V_{DS} = 400 V, I_D = 18 A, V_{GS} = 10 V (Note 4)	–	66	–	nC
Q_{gs}	Gate−to−Source Gate Charge		–	22	–	nC
Q_{gd}	Gate−to−Drain “Miller” Charge		–	26	–	nC
ESR	Equivalent Series Resistance	f = 1 MHz	–	2.4	–	Ω
SWITCHING CHARACTERISTICS						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 400 V, I_D = 18 A, V_{GS} = 10 V, R_g = 4.7 Ω (Note 4)	–	29.7	–	ns
t_r	Turn-On Rise Time		–	24.7	–	ns
$t_{d(off)}$	Turn-Off Delay Time		–	74.6	–	ns
t_f	Turn-Off Fall Time		–	3.2	–	ns
SOURCE-DRAIN DIODE CHARACTERISTICS						
I_S	Maximum Continuous Source−to−Drain Diode Forward Current		–	–	36	A
I_{SM}	Maximum Pulsed Source−to−Drain Diode Forward Current		–	–	90	A
V_{SD}	Source−to−Drain Diode Forward Voltage	V_{GS} = 0 V, I_{SD} = 18 A	–	–	1.3	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, I_{SD} = 18 A, dI_F/dt = 100 A/μs	–	91	–	ns
Q_{rr}	Reverse Recovery Charge		–	363	–	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Essentially independent of operating temperature typical characteristics.

TYPICAL CHARACTERISTICS

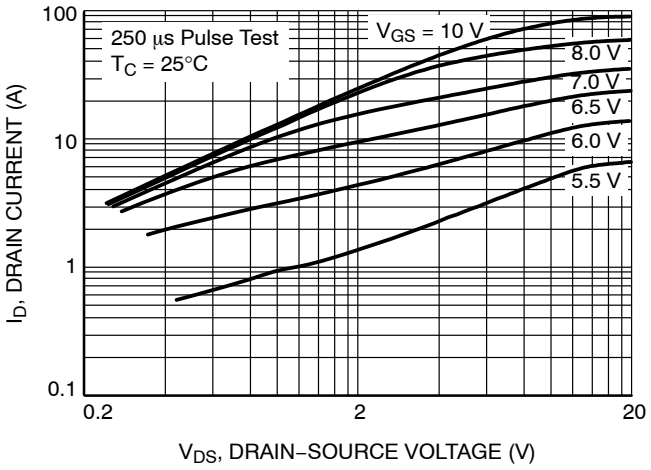


Figure 1. On−Region Characteristics 25°C

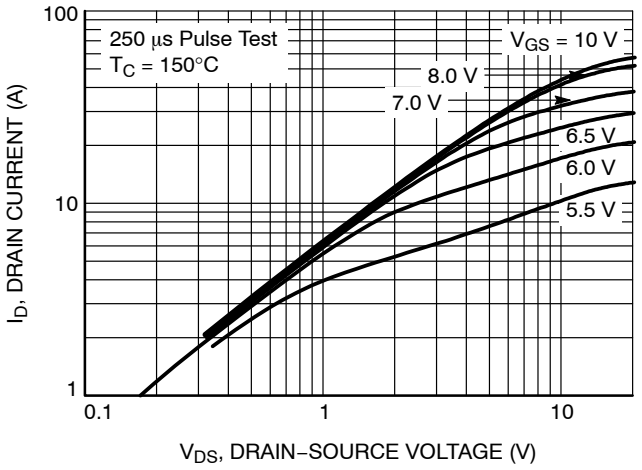


Figure 2. On−Region Characteristics 150°C

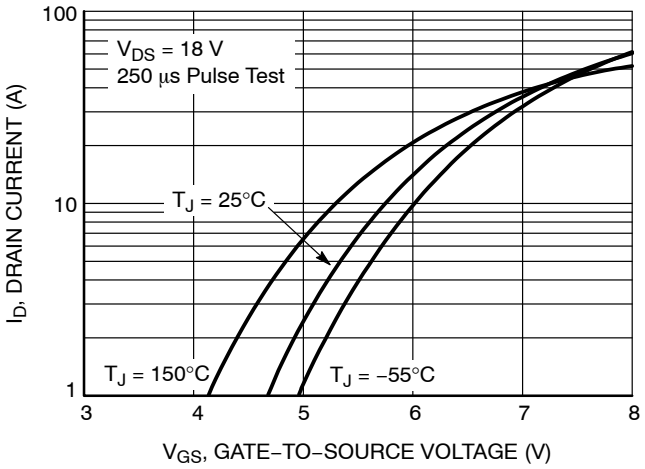


Figure 3. Transfer Characteristics

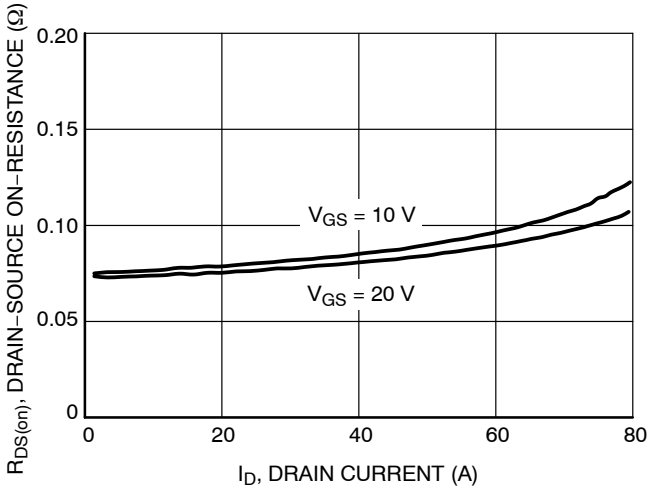


Figure 4. On−Resistance Variation vs. Drain Current and Gate Voltage

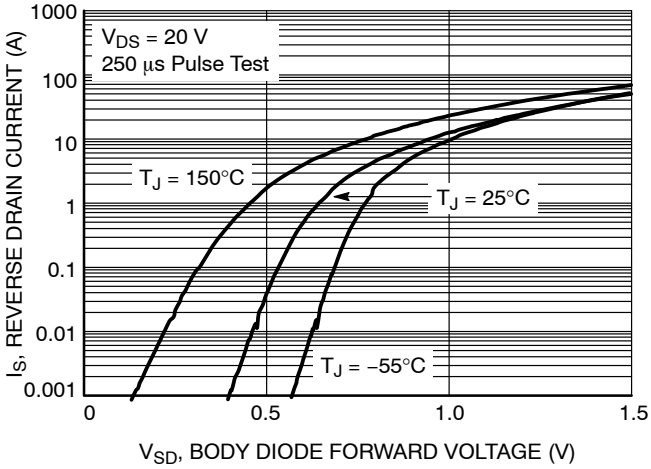


Figure 5. Body Diode Forward Voltage Variation vs. Source Current and Temperature

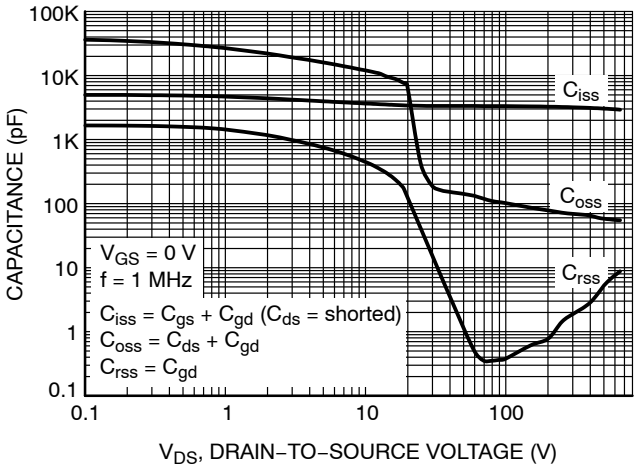


Figure 6. Capacitance Characteristics

TYPICAL CHARACTERISTICS

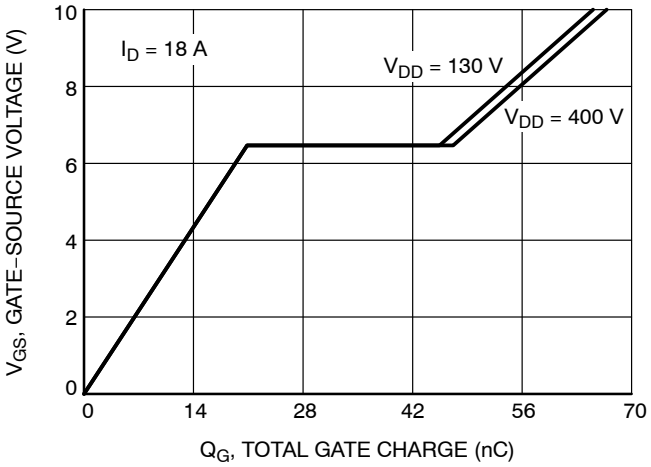


Figure 7. Gate Charge Characteristics

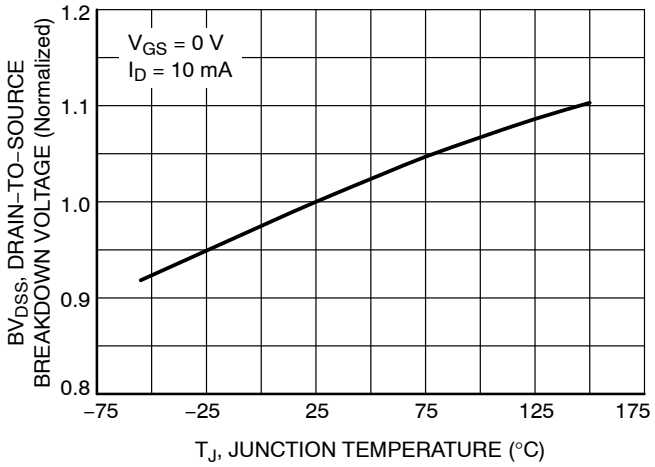


Figure 8. Breakdown Voltage Variation vs. Temperature

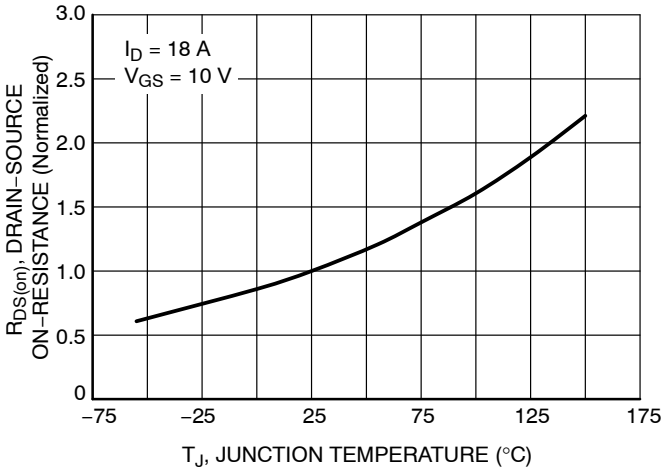


Figure 9. On−Resistance Variation vs. Temperature

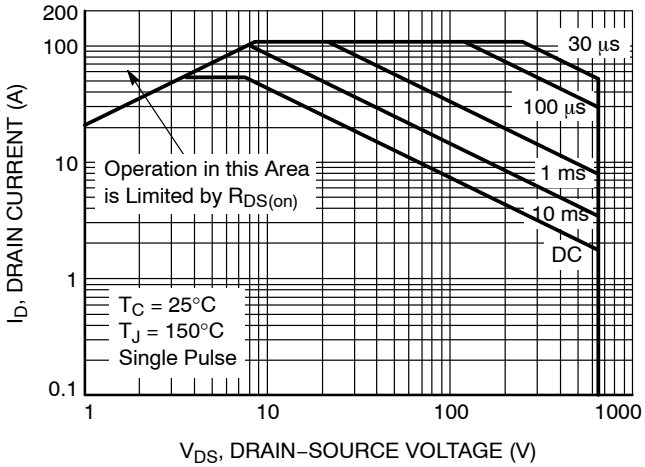


Figure 10. Maximum Safe Operating Area

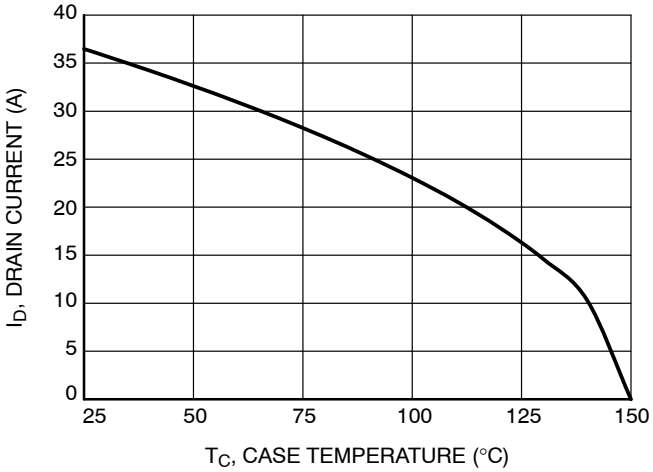


Figure 11. Maximum Drain Current vs. Case Temperature

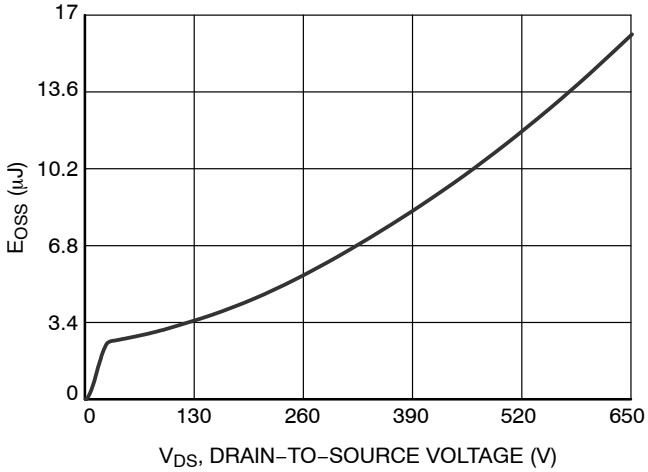


Figure 12. E_{OSS} vs. Drain−to−Source Voltage

TYPICAL CHARACTERISTICS

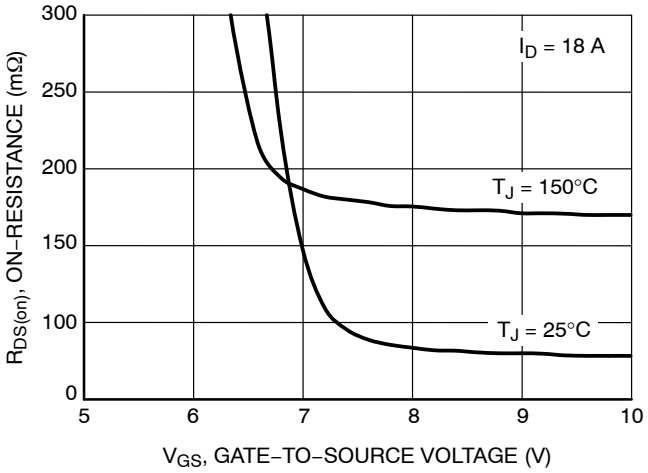


Figure 13. $R_{DS(on)}$ vs. Gate Voltage

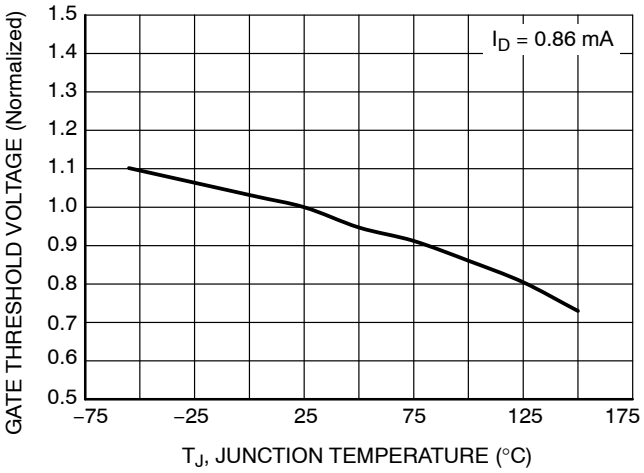
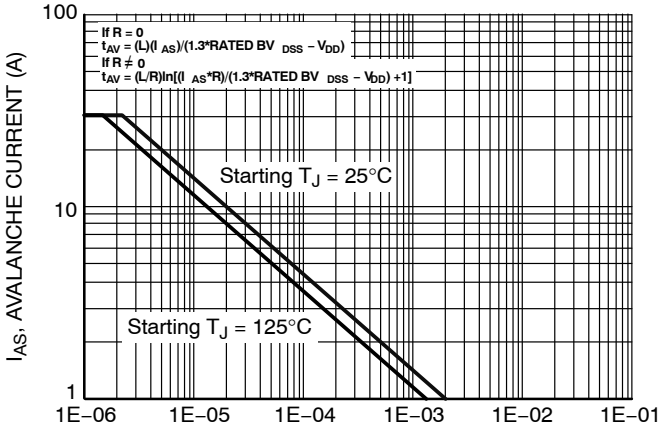


Figure 14. Normalized Gate Threshold Voltage vs. Temperature



NOTE: Refer to Fairchild Application Notes AN7514 and AN7515

Figure 15. Unclamped Inductive Switching Capability

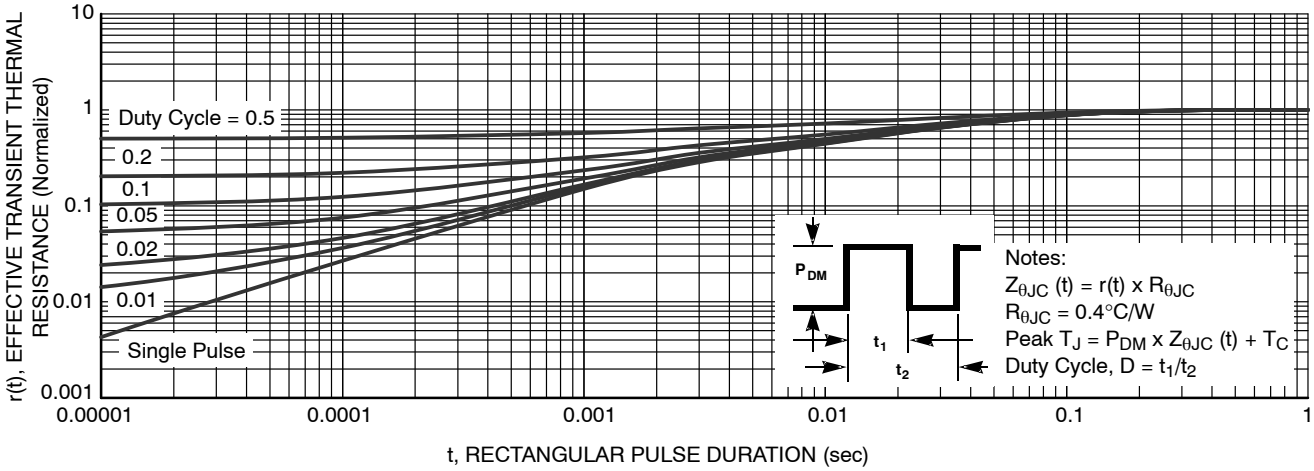


Figure 16. Transient Thermal Response

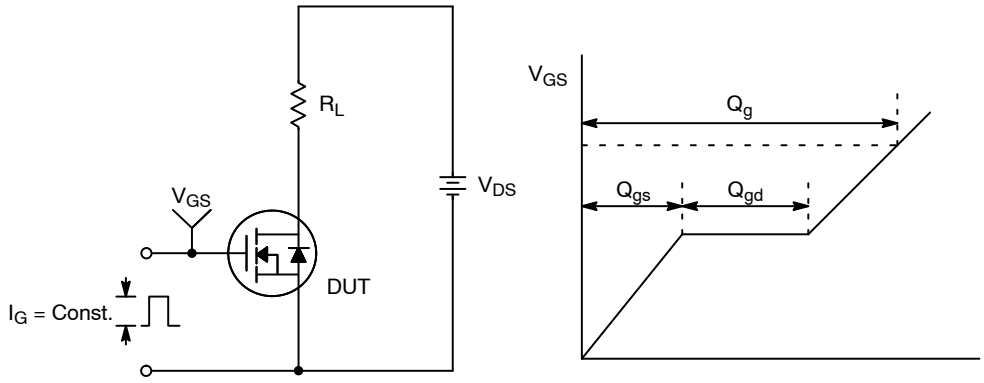


Figure 17. Gate Charge Test Circuit & Waveform

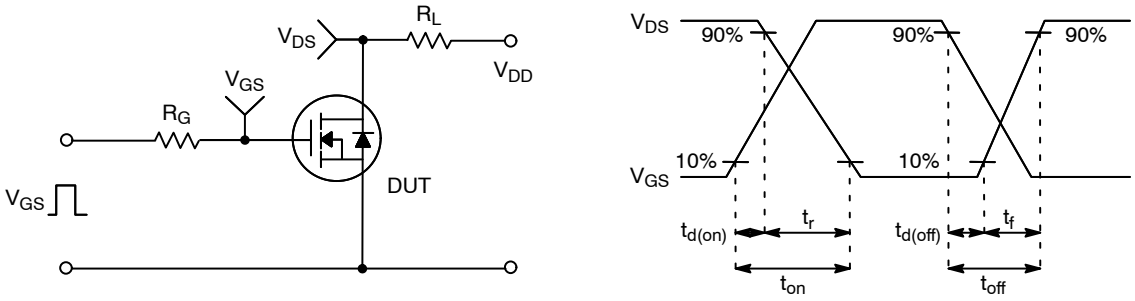


Figure 18. Resistive Switching Test Circuit & Waveforms

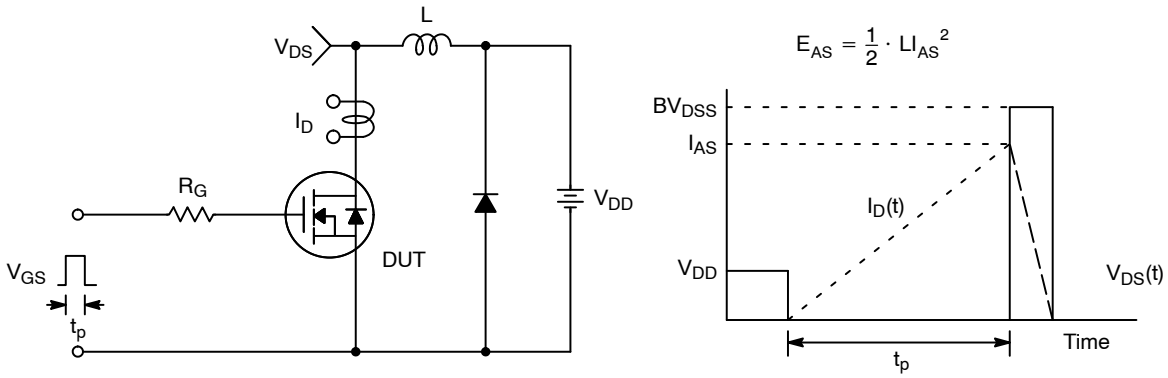


Figure 19. Unclamped Inductive Switching Test Circuit & Waveforms

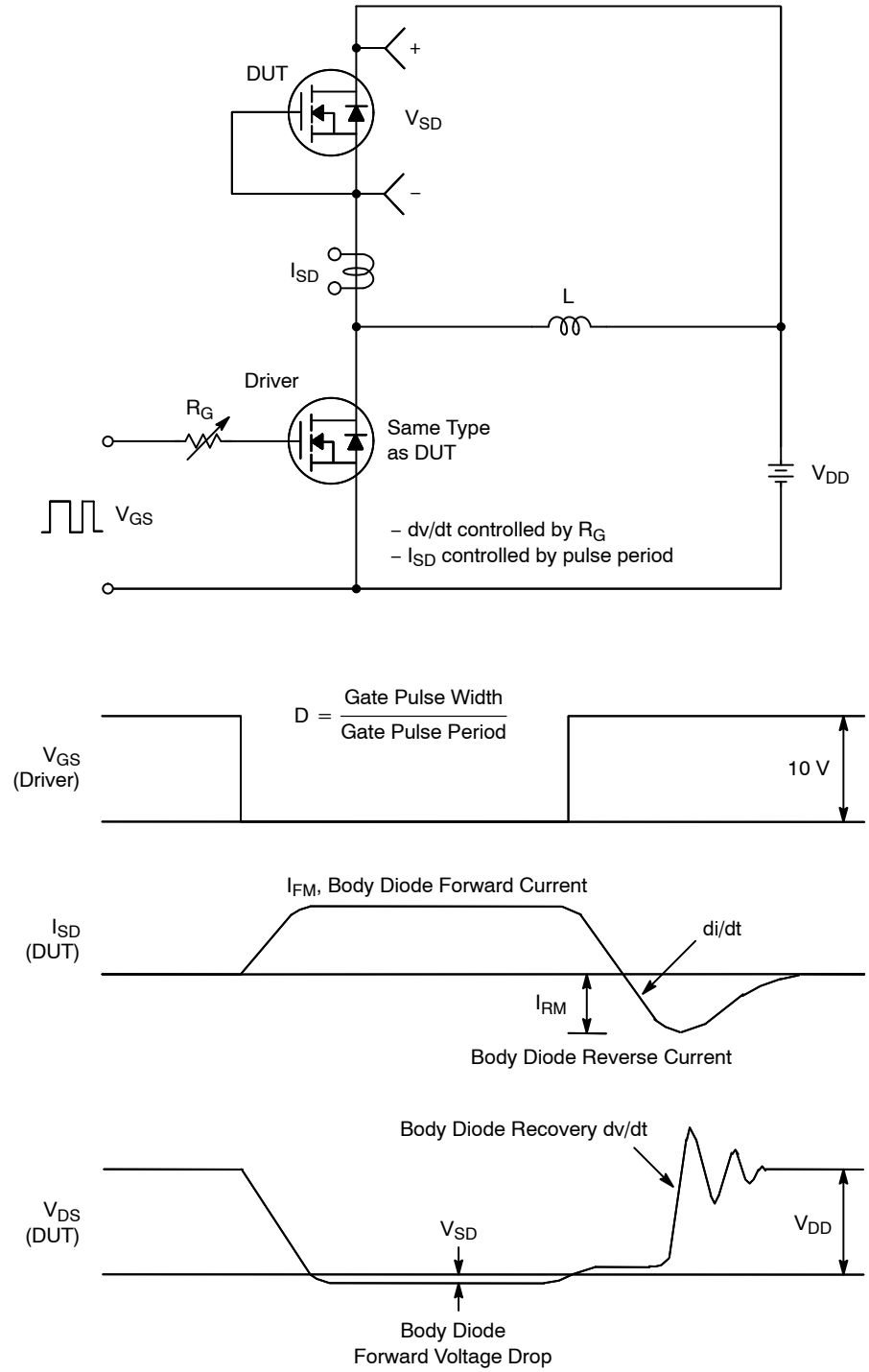
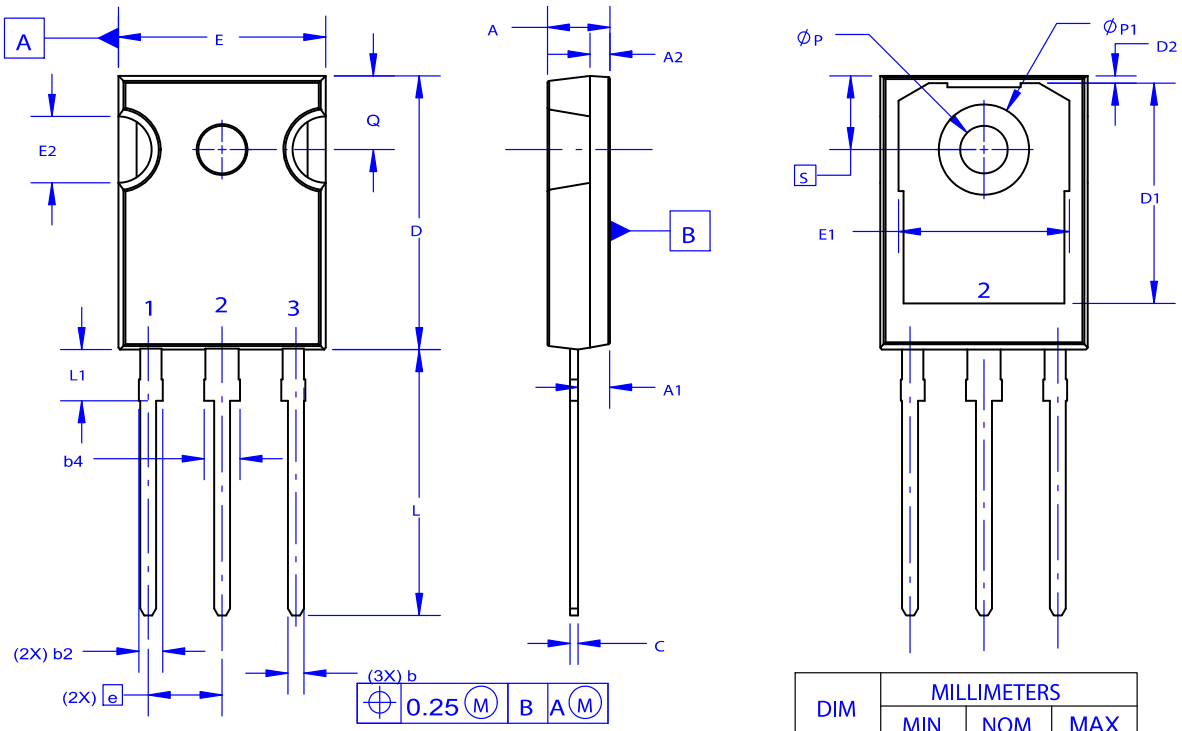


Figure 20. Peak Diode Recovery dv/dt Test Circuit & Waveforms

SUPERFET and FRFET are a registered trademarks of Semiconductor Components Industries, LLC (SCILLC) or its subsidiaries in the United States and/or other countries.

PACKAGE DIMENSIONS

TO−247−3LD
CASE 340CX
ISSUE A



NOTES: UNLESS OTHERWISE SPECIFIED.

A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
B. ALL DIMENSIONS ARE IN MILLIMETERS.
C. DRAWING CONFORMS TO ASME Y14.5 - 2009.
D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.58	4.70	4.82
A1	2.20	2.40	2.60
A2	1.40	1.50	1.60
D	20.32	20.57	20.82
E	15.37	15.62	15.87
E2	4.96	5.08	5.20
e	~	5.56	~
L	19.75	20.00	20.25
L1	3.69	3.81	3.93
ØP	3.51	3.58	3.65
Q	5.34	5.46	5.58
S	5.34	5.46	5.58
b	1.17	1.26	1.35
b2	1.53	1.65	1.77
b4	2.42	2.54	2.66
c	0.51	0.61	0.71
D1	13.08	~	~
D2	0.51	0.93	1.35
E1	12.81	~	~
ØP1	6.60	6.80	7.00

onsemi, ONSEMI , and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi's** product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent−Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as−is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT
North American Technical Support:
Voice Mail: 1 800−282−9855 Toll Free USA/Canada
Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:
Phone: 00421 33 790 2910
For additional information, please contact your local Sales Representative

◊

ENTEGRECİ

Bu belge www.entegreci.com üzerinden sunulmaktadır.

Elektronik komponent tedarikinde Entegreci

Entegreci, Eskişehir merkezli, Türkiye geneline satış yapan bir elektronik komponent mağazasıdır. Entegreler (IC), mikrodenetleyiciler, transistörler, diyotlar, pasif elemanlar, konnektörler, modüller ve geliştirme kartları tek adetten seri üretim adetlerine kadar satılır. Ürün sayfalarında güncel stok durumunu, fiyatı ve datasheet bağlantısını bulabilirsiniz.

Parça koduyla arama

Üretici parça numarasını yazın; stok ve fiyatı hemen görün.

www.entegreci.com

Ürün kategorileri

Entegreden kapasitöre tüm elektronik komponent kategorileri.

Kategorilere göz atın

Üreticiler

Aradığınız üreticinin ürünlerini tek sayfada inceleyin.

Üreticileri görün

Toplu alım ve teklif

Listede olmayan ya da yüksek adetli parçalar için teklif isteyin.

Teklif isteyin

www.entegreci.com | **destek@entegreci.com** | **0850 305 90 34**

Entegreci is an online electronic components store based in Türkiye. Search by manufacturer part number to see stock, prices and datasheets for integrated circuits, microcontrollers, transistors, passive components and connectors, or request a quote for parts that are not listed.

Bu sayfa Entegreci tarafından eklenmiştir. Belgenin önceki sayfaları asıl yayıncısına aittir ve içeriği değiştirilmemiştir; en güncel sürüm için belgenin yayıncısına başvurun.